

Sheet 1 of 1

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 119498		APPLICATION NO. 10/826,354	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)				APPLICANT Hiromi OTOMA		EX: Chuc TRAN	
				FILING DATE April 19, 2004		GROUP <del>2828</del> 2821	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
CT	1.	JP A 2002-185079 w/abstract & transl.	6/28/2002	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
CT	2.	Kenichi IGA; "Surface Emitting Laser"; IEICE Transactions C-1, Vol. J81-C-1, No. 9; September 1998; pp 483-493					
	3.	H. OTOMA et al.; "Fabrication and Performance of 12 X 12 Matrix-Addressed 780nm Oxide-Confined Vcsel Array"; Bulletin of Solid State Physics and Applications; Vol. 5, No. 1.; 1999; pp 11-15					
CT	4.	Nobuaki UEKI et al.; "Single-Transverse-Mode 3.4-mW Emission of Oxide-confined 780-nm Vcsel's"; IEEE Photonics Technology Letters; Vol. 11, No. 12; December 1999; pp 1539-1541					
	5.	Jun SAKURAI et al.; "10 Gb/s Surface Emission Semiconductor Laser"; Electronic Materials, Vol. 41, No. 11; November 2002; pp 49-52					
CT	6.	M. Grabherr et al.; "Efficient Single-Mode Oxide-Confined GaAs VCSEL's Emitting in the 850-nm Wavelength Regime"; IEEE Photonics Technology Letters; Vol. 9, No. 10.; October 1997; pp 1304-1306					
	7.	Aaron et al.; "Aperture Placement Effects in Oxide-Defined Vertical-Cavity Surface-Emitting Lasers"; IEEE Photonics Technology Letters; Vol. 10, No. 10; October 1998; pp 1362-1364					
EXAMINER  /Chuc Tran/				DATE CONSIDERED  05/15/2006			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: July 29, 2004